

## N-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY								
Part Number	V <sub>(BR)DSS</sub> Min (V)	$r_{DS(on)}$ Max ( $\Omega$ )	V <sub>GS(th)</sub> (V)	I <sub>D</sub> (A)				
2N7000		5 @ V <sub>GS</sub> = 10 V	0.8 to 3	0.2				
2N7002	60	7.5 @ V <sub>GS</sub> = 10 V	1 to 2.5	0.115				
VQ1000J		5.5 @ V <sub>GS</sub> = 10 V	0.8 to 2.5	0.225				
VQ1000P		5.5 @ V <sub>GS</sub> = 10 V	0.8 to 2.5	0.225				
BS170		5 @ V <sub>GS</sub> = 10 V	0.8 to 3	0.5				

### **FEATURES**

Low On-Resistance: 2.5 ΩLow Threshold: 2.1 V

Low Input Capacitance: 22 pFFast Switching Speed: 7 ns

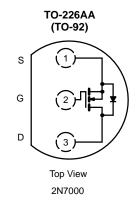
• Low Input and Output Leakage

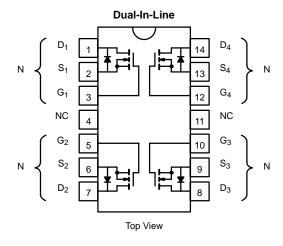
### **BENEFITS**

- Low Offset Voltage
- Low-Voltage Operation
- Easily Driven Without Buffer
- High-Speed Circuits
- Low Error Voltage

### **APPLICATIONS**

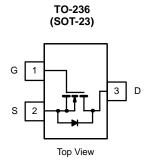
- Direct Logic-Level Interface: TTL/CMOS
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.
- Battery Operated Systems
- Solid-State Relays





Plastic: VQ1000J

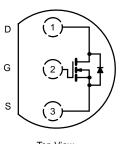
Sidebraze: VQ1000P



Marking Code: 72wll

72 = Part Number Code for 2N7002 w = Week Code # = Lot Traceability

### TO-92-18RM (TO-18 Lead Form)



Top View

BS170

# 2N7000/2N7002, VQ1000J/P, BS170

# Vishay Siliconix



				T	S OTHERWISE NOT Single		Total Quad	BS170	T
Parameter		Symbol	2N7000	2N7002	VQ1000J	VQ1000P	VQ1000J/P		Unit
Drain-Source Voltage		$V_{DS}$	60	60	60	60		60	
Gate-Source Voltage—Non-Repetitive		$V_{GSM}$	±40	±40	±30			±25	٧
Gate-Source Voltage—Continuous		$V_{GS}$	±20	±20	±20	±20		±20	1
Continuous Drain Current (T <sub>J</sub> = 150°C)	T <sub>A</sub> = 25°C	<b>.</b>	0.2	0.115	0.225	0.225		0.5	
	T <sub>A</sub> = 100°C	I <sub>D</sub>	0.13	0.073	0.14	0.14		0.175	Α
Pulsed Drain Current <sup>a</sup>		I <sub>DM</sub>	0.5	0.8	1	1			1
D 01 1 11	T <sub>A</sub> = 25°C		0.4	0.2	1.3	1.3	2	0.83	
Power Dissipation	T <sub>A</sub> = 100°C	P <sub>D</sub>	0.16	0.08	0.52	0.52	0.8		W
Thermal Resistance, Junction-to-Ambient		R <sub>thJA</sub>	312.5	625	96	96	62.5	156	°C/W
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150						°C

					Lin	nits			
				2N7000		2N7002		1	
Parameter	Symbol	<b>Test Conditions</b>	Typa	Min	Max	Min	Max	Unit	
Static			•	•		•	•	•	
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 \text{ V}, I_D = 10 \mu\text{A}$	70	60		60		T	
	.,	$V_{DS} = V_{GS}$ , $I_D = 1 \text{ mA}$	2.1	0.8	3			V	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 0.25 \text{ mA}$	2.0			1	2.5	1	
Gate-Body Leakage		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 15 \text{ V}$			±10				
	I <sub>GSS</sub>	$V_{DS}$ = 0 V, $V_{GS}$ = $\pm 20$ V					±100	nA	
Zero Gate Voltage Drain Current		$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}$			1				
	I <sub>DSS</sub>	T <sub>C</sub> = 125°C			1000			1 .	
		V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V					1	μΑ	
		T <sub>C</sub> = 125°C					500	1	
0.01.1.0		V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 4.5 V	0.35	0.075				A	
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 7.5 V, V <sub>GS</sub> = 10 V	1			0.5			
		$V_{GS} = 4.5 \text{ V}, I_D = 0.075 \text{ A}$	4.5		5.3				
		$V_{GS} = 5 \text{ V}, I_D = 0.05 \text{ A}$	3.2				7.5	1	
Drain-Source On-Resistance <sup>b</sup>	r <sub>DS(on)</sub>	T <sub>C</sub> = 125°C	5.8				13.5	Ω	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 0.5 A	2.4		5		7.5	1	
		T <sub>J</sub> = 125°C	4.4		9		13.5	1	
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.2 A		100		80			
Common Source Output Conductance <sup>b</sup>	gos	$V_{DS} = 5 \text{ V}, I_D = 0.05 \text{ A}$	0.5					- mS	
Dynamic				-		-	-		
Input Capacitance	C <sub>iss</sub>		22		60		50		
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}$ f = 1  MHz			25		25	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	1 — 1 1911 12			5		5	1	

Notes a. Pulse width limited by maximum junction temperature. b.  $t_p \leq 50~\mu s.$ 



# 2N7000/2N7002, VQ1000J/P, BS170

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SPECIFICATIONS—2N7000 AND 2N7002 (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)											
				Limits							
				2N7000 2N7002							
Parameter	Symbol	Test Conditions	Typa	Min	Max	Min	Max	Unit			
Switching <sup>d</sup>				-							
Turn-On Time	t <sub>ON</sub>	$V_{DD} = 15 \text{ V}, R_{L} = 25 \Omega$	7		10						
Turn-Off Time	t <sub>OFF</sub>	$I_D \cong 0.5 \text{ A}, V_{GEN} = 10 \text{ V}, R_G = 25 \Omega$	7		10			ns			
Turn-On Time	t <sub>ON</sub>	$V_{DD} = 30 \text{ V}, R_{L} = 150 \Omega$	7				20	115			
Turn-Off Time	t <sub>OFF</sub>	$I_D \cong 0.2 \text{ A}, V_{GEN} = 10 \text{ V}, R_G = 25 \Omega$	11				20				

					Lin	nits			
				VQ1000J/P		BS170		1	
Parameter	Symbol	<b>Test Conditions</b>	Typa	Min	Max	Min	Max	Unit	
Static	•		•	•					
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 \text{ V}, I_D = 100 \mu\text{A}$	70	60		60		Ι.,	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 1$ mA	2.1	8.0	2.5	0.8	3	V	
		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 10 \text{ V}$			±100				
Gate-Body Leakage	I <sub>GSS</sub>	T <sub>J</sub> = 125°C			±500			nA	
-	T	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 15 \text{ V}$					±10	1	
Zero Gate Voltage Drain Current		V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V					0.5	μΑ	
	I <sub>DSS</sub>	V <sub>DS</sub> = 48 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125°C			500				
		V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V			10				
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	$V_{DS} = 10 \ V, V_{GS} = 10 \ V$	1	0.5				Α	
	r <sub>DS(on)</sub>	$V_{GS} = 5 \text{ V}, I_D = 0.2 \text{ A}$	4		7.5				
		$V_{GS} = 10 \text{ V}, I_D = 0.2 \text{ A}$	2.3				5	1	
Drain-Source On-Resistance <sup>b</sup>		$V_{GS} = 10 \text{ V}, I_D = 0.3 \text{ A}$	2.3		5.5			Ω	
		T <sub>J</sub> = 125°C	4.2		7.6			1	
Forward Transconductance <sup>b</sup>	9fs -	$V_{DS} = 10 \text{ V}, I_D = 0.2 \text{ A}$				100			
Forward Transconductance		$V_{DS} = 10 \ V, I_{D} = 0.5 A$		100				mS	
Common Source Output Conductance <sup>b</sup>	9 <sub>os</sub>	$V_{DS} = 5 \text{ V}, I_D = 0.05 \text{ A}$	0.5					1	
Dynamic				-					
Input Capacitance	C <sub>iss</sub>		22		60		60		
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =25 V, V <sub>GS</sub> = 0 V f = 1 MHz	11		25			pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	1 - 1 1911 12			5			1	
Switching <sup>d</sup>	•		•	•					
Turn-On Time	t <sub>ON</sub>	$V_{DD} = 15 \text{ V, R}_{I} = 23 \Omega$	7		10				
Turn-Off Time	t <sub>OFF</sub>	$I_D \approx 0.6 \text{ A}, V_{GEN} = 10 \text{ V}, R_G = 25 \Omega$	7		10			1	
Turn-On Time	t <sub>ON</sub>	$V_{DD} = 25 \text{ V}, R_{L} = 125 \Omega$	7				10	ns	
Turn-Off Time	toff	$I_D \cong 0.2 \text{ A, V}_{GEN} = 10 \text{ V, R}_G = 25 \Omega$					10	1	

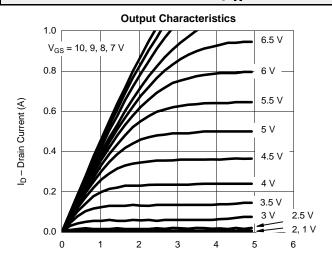
VNBF06

Notes a. For DESIGN AID ONLY, not subject to production testing. b. Pulse test: PW  $\leq 80~\mu s$  duty cycle  $\leq 1\%$ . c. This parameter not registered with JEDEC. d. Switching time is essentially independent of operating temperature.

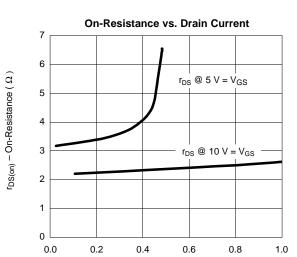
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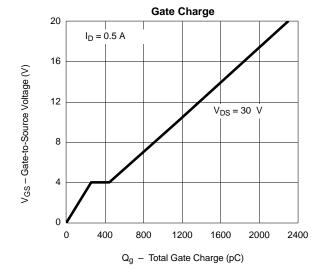
### TYPICAL CHARACTERISTICS (TA = 25°C UNLESS OTHERWISE NOTED)

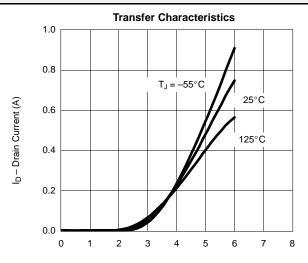


V<sub>DS</sub> - Drain-to-Source Voltage (V)

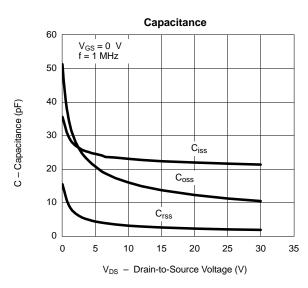


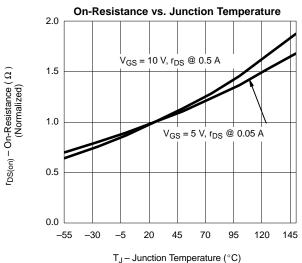
I<sub>D</sub> - Drain Current (A)





V<sub>GS</sub> - Gate-to-Source Voltage (V)

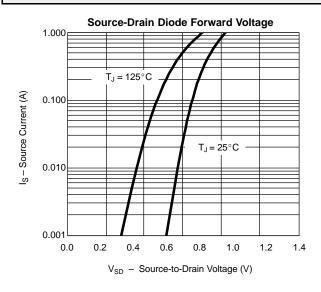


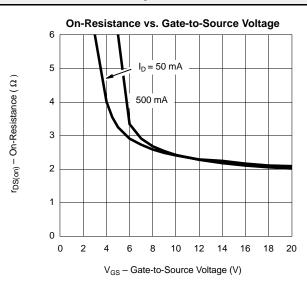


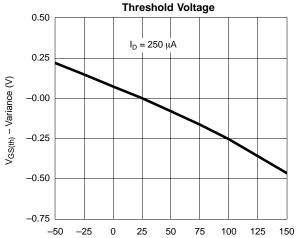


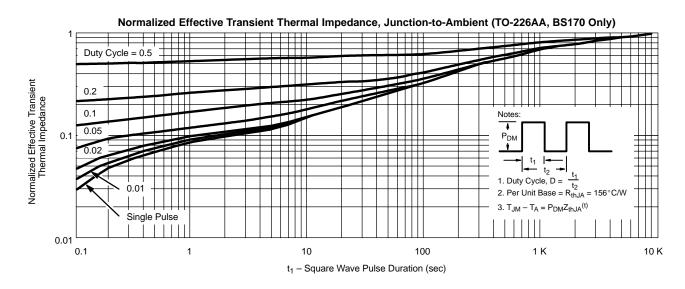
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## TYPICAL CHARACTERISTICS (TA = 25°C UNLESS OTHERWISE NOTED)











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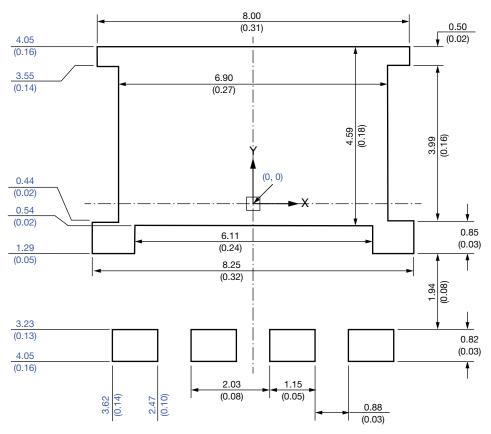
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# Recommended Minimum PADs for PowerPAK® 8 x 8L Single



Dimensions in millimeters (inches)

### Note

• Linear dimensions are in black, the same information is provided in ordinate dimensions which are in blue.



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